

ABSTRACT OF THE DISCLOSURE

A semiconductor device and a method of manufacturing thereof can be gained wherein the occurrence of defects can be prevented and it is possible to reduce the manufacturing cost. The semiconductor device 5 includes a capacitor electrode, an insulating layer and a wiring layer. The capacitor electrode is formed on the semiconductor substrate. The insulating film which is formed on the capacitor electrode has a trench which exposes part of the capacitor electrode and has an upper surface. The wiring layer fills in the inside of the trench, has an upper surface and 10 is connected with the capacitor electrode. The upper surface of the wiring layer is located on approximately the same plane as the upper surface of the insulating film.